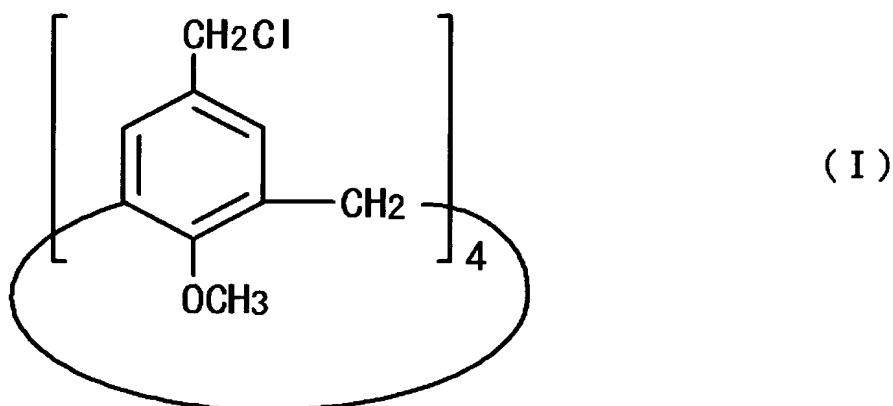


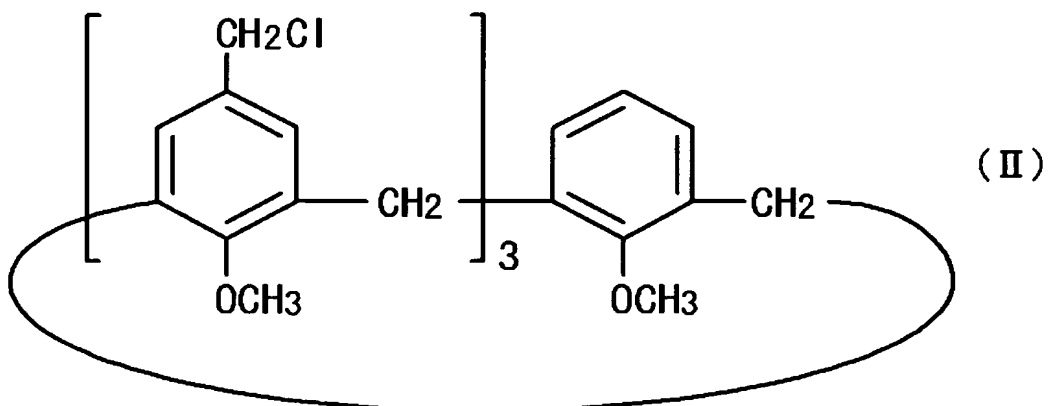
CLAIMS

1. A calixarene composition comprising at least one of 5,11,17,23 - tetrachloromethyl - 25,26,27,28 - tetramethoxycalix [4] arene (CMC4AOMe) represented by the structural formula (I) of the following chemical formula 1 and 5,11,17 - trichloromethyl - 25,26,27,28 - tetramethoxycalix [4] arene (CMC3AOMe) represented by the structural formula (II) of the following chemical formula 2.

10 [Chemical Formula 1]

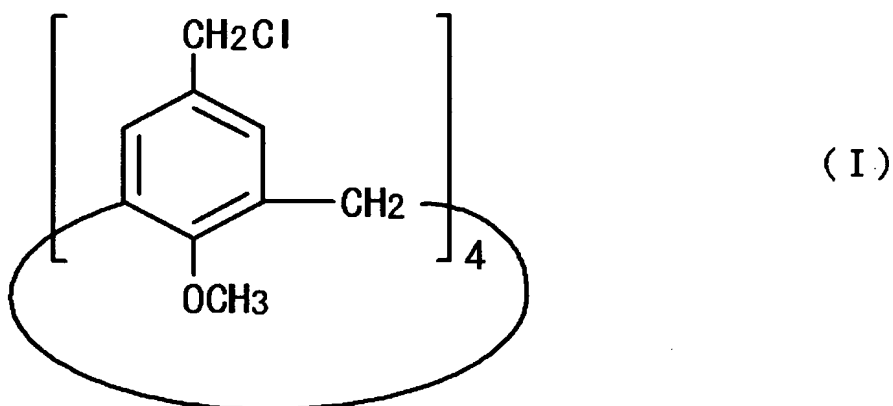


[Chemical Formula 2]

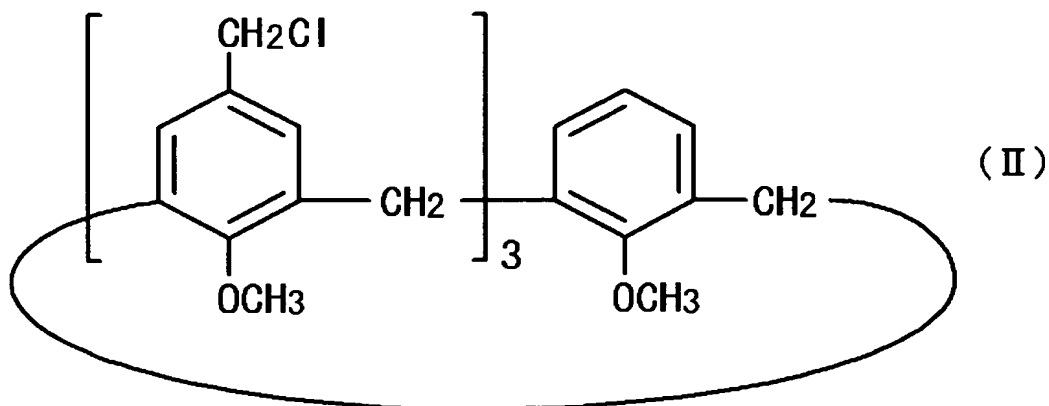


2. A resist comprising at least one of 5,11,17,23 - tetrachloromethyl - 25,26,27,28 - tetramethoxycalix [4] arene (CMC4AOMe) represented by the structural formula (I) of the following chemical formula 3 and 5,11,17 - trichloromethyl - 25,26,27,28 - tetramethoxycalix [4] arene (CMC3AOMe) represented by the structural formula (II) of the following chemical formula 4.

10 [Chemical Formula 3]

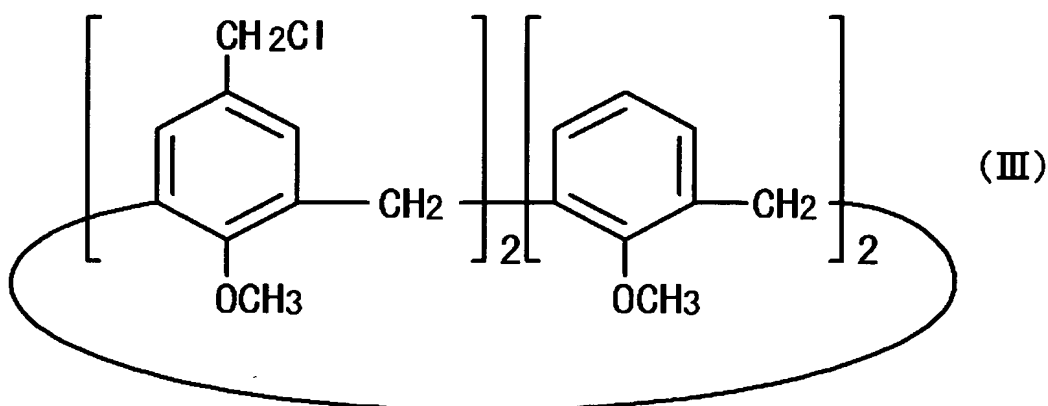


[Chemical Formula 4]

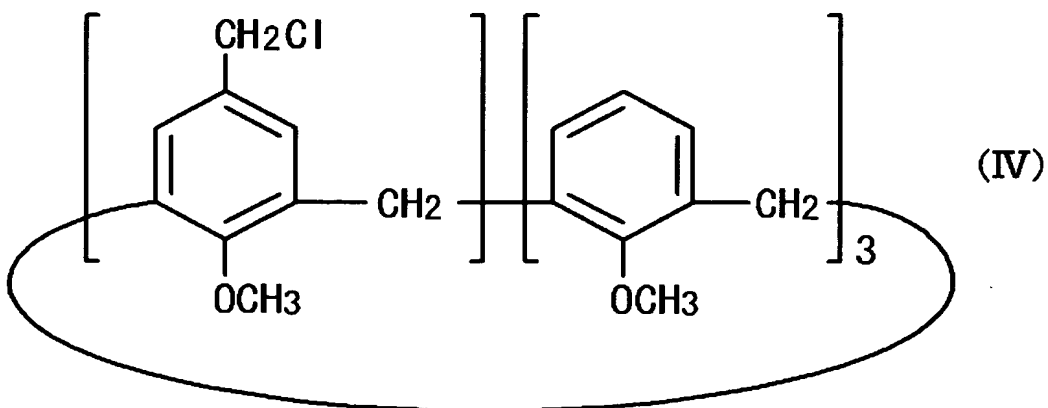


3. The resist according to claim 2, further comprising at least one of 5,11 - dichloromethyl - 25,26,27,28 - tetramethoxycalix [4] arene (CMC2AOMe) 5 represented by the structural formula (III) of the following chemical formula 5 and 5 - monochloromethyl - 25,26,27,28 - tetramethoxycalix [4] arene (CMC1AOMe) represented by the structural formula (IV) of the following chemical formula 6 is provided.

10 [Chemical Formula 5]



[Chemical Formula 6]



4. The resist according to claim 2 or 3, further comprising at least one of oligomer and organic polymer compound.

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5. The resist according to any one of claims 2 to 4, which is exposed by the irradiation of at least one of electronic beam, X-ray, ion beam and atomic beam.

10 6. The resist according to any one of claims 2 to 5, further comprising, at least one solvent selected from the group consisting of ethyl lactate (EL), propylene glycol monomethyl ether (PGME), propylene glycol monomethyl ether acetate (PGMEA), ethyl propionate, n-
15 butyl acetate and 2-heptanone.

7. A method for forming a resist pattern comprising the following steps of coating the resist according to claim 6 on a substrate, exposing said resist to a
20 radioactive ray; and a step developing said resist.

8. The method according to claim 7,
Wherein said radioactive ray is any of electronic beam, X-ray, ion beam and atomic beam.

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9. The method according to claim 7 or 8,
wherein said developing step is carried out by

using a developer comprising at least one selected from the group consisting of ethyl lactate (EL), propylene glycol monomethyl ether (PGME), propylene glycol monomethyl ether acetate (PGMEA), ethyl
5 propionate, n-butyl acetate, 2-heptanone and tetramethyl ammonium hydroxide.

10. A method for hyperfine processing comprising the steps of forming a resist pattern using the resist
10 pattern forming method according to any one of claims 7 to 9; and performing a processing on said substrate with said resist pattern as a mask.